ABSTRACT OF THE DISCLOSURE

A bonded wafer is produced by implanting ions of a light element into a wafer for active layer to a predetermined depth position to form an ion implanted layer, bonding the wafer for active layer to a wafer for support substrate directly or through an insulating film of not more than 50 nm, exfoliating the wafer for active layer at the ion implanted layer and thinning an active layer exposed through the exfoliation to form the active layer having a predetermined thickness, in which the thickness of the active layer before the thinning is not more than 750 nm and an elongation of slip dislocation in a strength test of the wafer for active layer before the bonding is not more than 100 μm at a predetermined thickness.